

BYV60W-600P Ultrafast power diode

Rev.02 - 18 May 2023

Product data sheet

1. General description

Ultrafast power diode in a 2-lead TO247 plastic package.

2. Features and benefits

- · Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT
- High operating temperature capability (T_{i (max)} = 175°C)

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

Symbol	Parameter	Conditions			luce		Unit
		Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	00		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 129 °C; Fig. 1; Fig. 2; Fig. 3	60			A	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse	120		A		
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600			A	
		t_{p} = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse	660		А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.6	V
Dynamic	characteristics					÷	
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 50 A/μs; T _i = 25 °C; <u>Fig. 7</u>		-	-	55	ns

5. Pinning information

Table 2. P	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	K A TO247-2L	

6. Ordering information

Table 3. Ordering information							
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
BYV60W-600P	TO247-2L	BYV60W-600PQ	Tube	30	TO247L-2L (L)	12-Nov-2020	
					TO247P-2L (P)	31-Mar-2023	

7. Marking

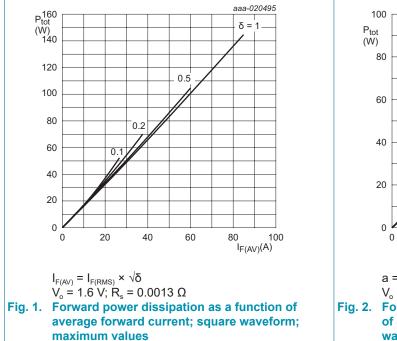
Table 4. Marking codes Type number Marking codes Assembly factory: L Assembly factory: P BYV60W-600P BYV60W BYV60W BYV60W BYV60W 600P PJLxxxxx xx PJPxxxxx xx

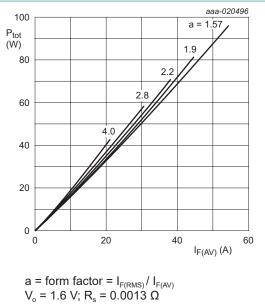
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

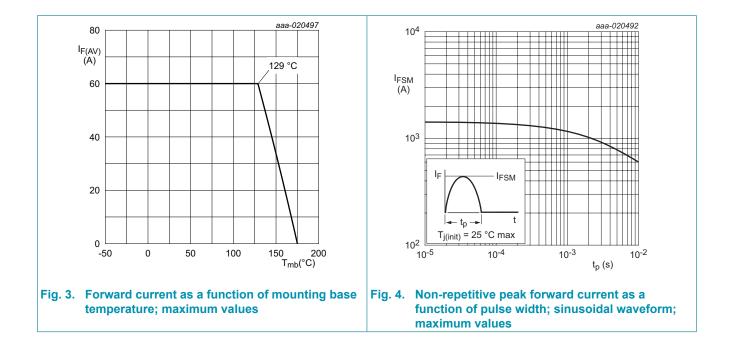
Symbol	Parameter	Conditions	Values	Unit
V _{RRM}	repetitive peak reverse voltage		600	V
V _{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 129 °C; Fig. 1; Fig. 2; Fig. 3	60	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse	120	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660	А
l ² t	limiting Joule-integral	SIN; t _p = 10 ms	1800	A ² s
T _{stg}	storage temperature		-55 to 175	°C
Tj	junction temperature		175	°C





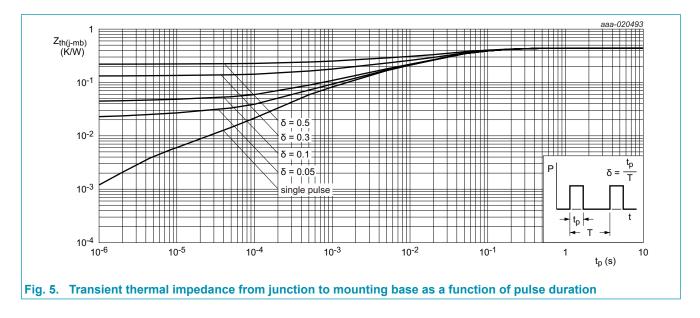


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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.44	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

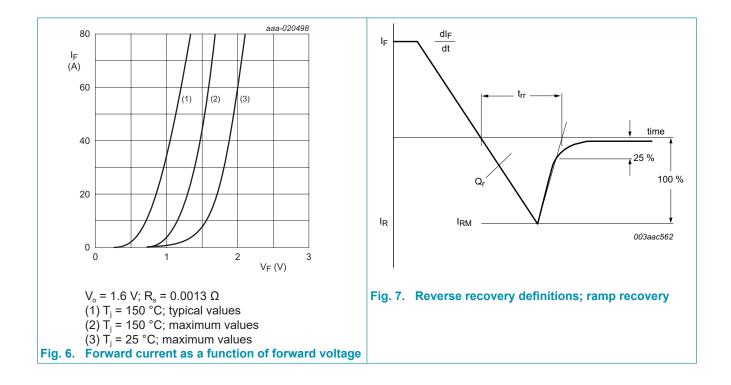


10. Characteristics

Symbol	Parameter	neter Conditions		Тур	Max	Unit
Static ch	aracteristics					
V _F	forward current	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.6	V
R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	143	-	nC
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	876	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	55	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	53	-	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	120	-	ns
I _{RM}	peak reverse recovery current	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	5.4	-	A
		$I_{F} = 60 \text{ A}; V_{R} = 400 \text{ V}; \text{ d}I_{F}/\text{d}t = 200 \text{ A}/\mu\text{s}; T_{j} = 125 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	14.5	-	A
as	non-repetitive avalanche energy	$I_R = 2.2 \text{ A}; T_{j(init)} = 25 \text{ °C}; L = 40 \text{ mH}$	-	97	-	mJ

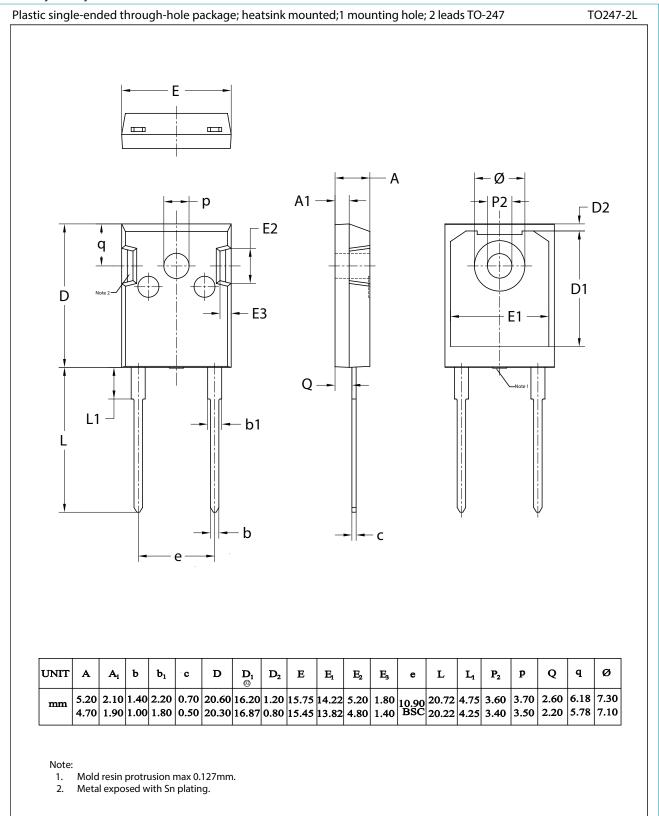
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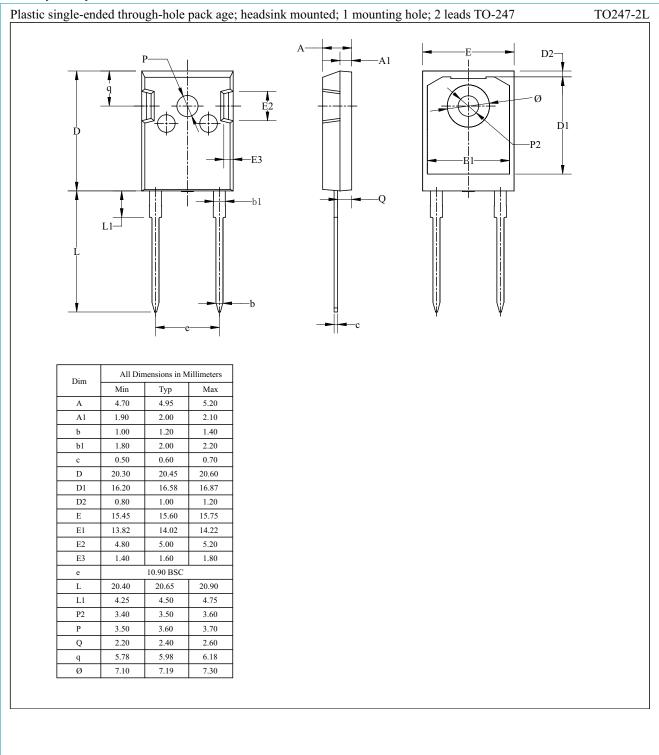


11. Package outline

Assembly factory: L



Assembly factory: P



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Ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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